

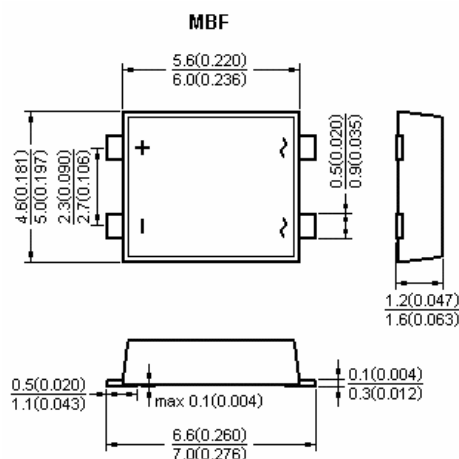
VOLTAGE RANGE: 20 - 100V
CURRENT: 1.0 A

Features

- Low profile package
- Ideal for automated placement
- Ultrafast reverse recovery time
- Low power losses, high efficiency
- Low forward voltage drop
- High surge capability
- High temperature soldering!
260 °C / 10 seconds at terminals

Mechanical Data

- Case: MBF molded plastic body over Schottky barrier chips



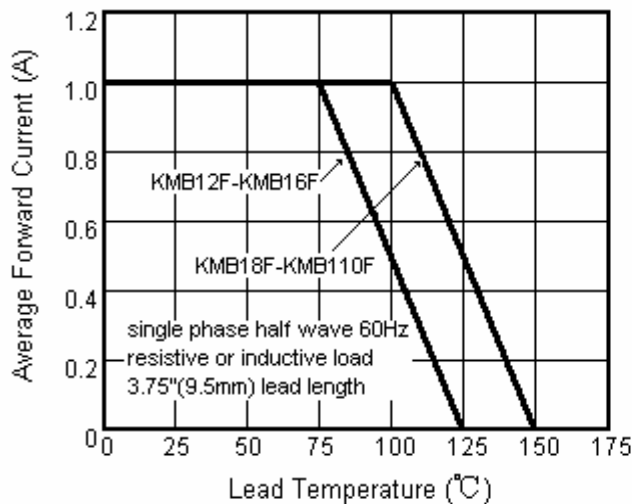
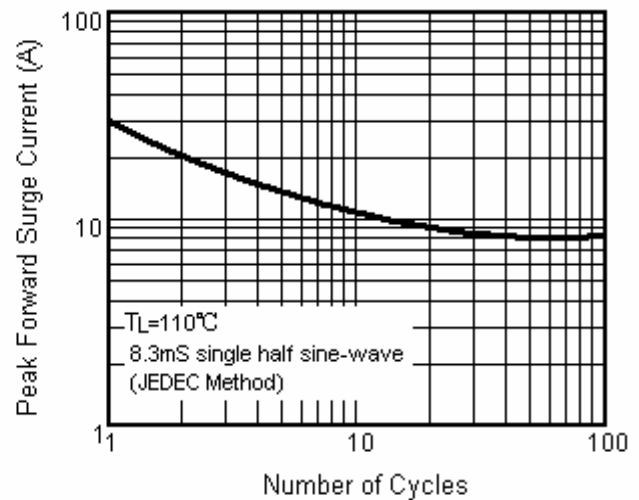
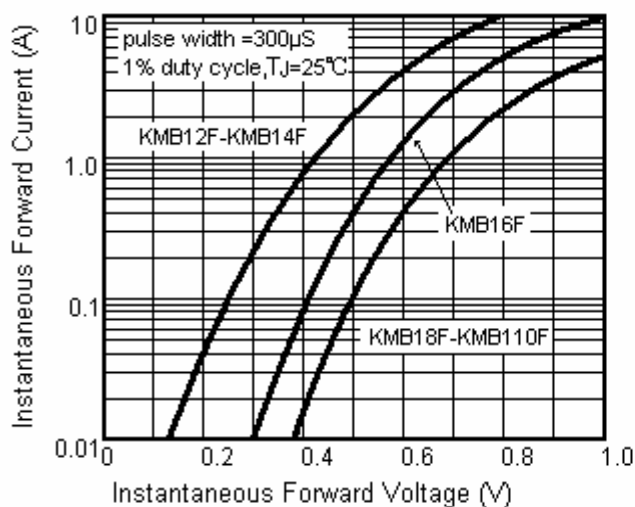
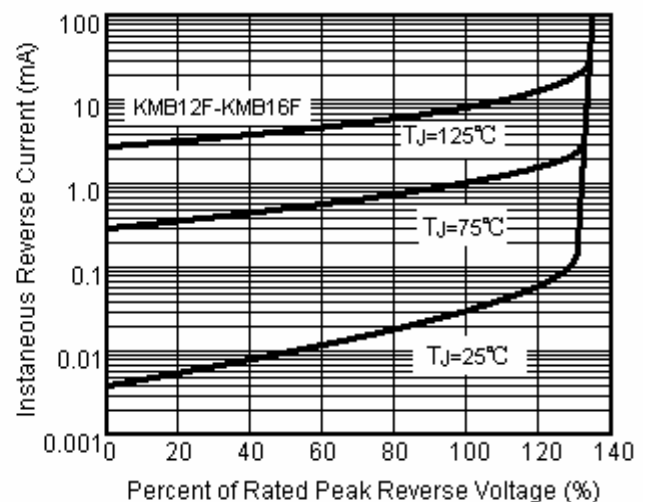
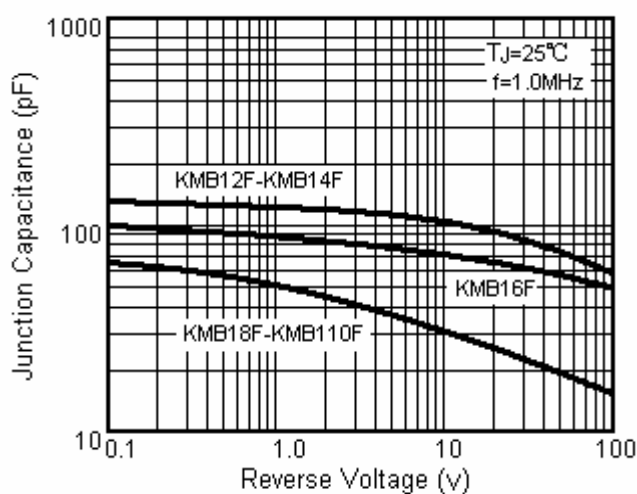
Dimensions in millimeters and (inches)

Maximum Ratings and Electrical Characteristics T_A = 25°C unless otherwise specified

Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

	Symbol	KMB12F	KMB14F	KMB16F	KMB18F	KMB110F	UNIT
Maximum repetitive peak reverse voltage	V _{RRM}	20	40	60	80	100	V
Maximum RMS voltage	V _{RMS}	14	28	42	56	70	V
Maximum DC blocking voltage	V _{DC}	20	40	60	80	100	V
Maximum average forward rectified current 0.2×0.2"(5.0×5.0mm)copper pad area	I _{F(AV)}	1.0					A
Peak forward surge current 8.3 ms single half sine-wave superimposed on rated load	I _{FSM}	30					A
Maximum instantaneous forward voltage at 1.0A	V _F	0.50	0.55	0.70	0.85		V
Maximum DC reverse current at Rated DC blocking voltage	I _R	0.5 20					mA
Typical Junction Capacitance at 4.0V, 1.0MHz	C _J	250			125		pF
Typical Thermal resistance (Note1)	R _{θJA} R _{θJL}	85 20					°C/W
Operating junction temperature range	T _J	-55 to +125					°C
Storage temperature range	T _{STG}	- 55 to +150					°C

Note: 1. Thermal resistance from junction to ambient and from junction to lead P.C.B. mounted on 0.2×0.2"(5.0×5.0mm)copper pad areas.

Fig.1 Forward Current Derating Curve

Fig.2 Maximum Non-Repetitive Peak Forward Surge Current

Fig.3 Typical Instantaneous Forward Characteristics

Fig.4A Typical Reverse Characteristics

Fig.5 Typical Junction Capacitance

Fig.4B Typical Reverse Characteristics
